MSKSEMI 美森科













ESD

T\/C

TSS

MOV

GDT

PIFD

LMV721/LMV722

Product specification





GENERAL DESCRIPTION

The LMV721/LMV722 families of products offer low voltage operation and rail-to-rail input and output, as well as excellent speed/power consumption ratio, providing an excellent bandwidth(8MHz), a slew rate of 6.5V/u s, and a quiescent current of 510uA/amplifier at 5.0V. The op-amps are unity gain stable and feature an ultr a-low input bias current.

The LMV721/LMV722 are designed to provide optimal performance in low-voltage systems. They provide rail-t o-rail I/O, and the maximum input offset voltage are 2.5mV for the devices. Their capacitive load capability is also good at low supply voltages. The operating range is from 2.2 V to 5.5 V.

The LMV721/LMV722 families of operational amplifiers are specified at the full temperature range of - 40°C to +125°C under single or dual power supplies of 2.2V to 5.5V.

Features

Input Offset Voltage: 2.5mV (MAX
 Low Supply Current: 510µA

(Vs=2.2V)

Supply Range: 2.2V to 5.5V

• Gain Bandwidth: 8MHz (V s=5V)

• Slew rate: 6.5V/µs (Vs=5V)

Rail-to-Rail Input and Output

Low Cost

Micro size Packages:

LMV721IDCKR-MS: SC70-5 LMV721IDBVR-MS: SOT23-5 LMV722IDR-MS: SOP-8

LMV722IDGKR-MS: MSOP-8

Applications

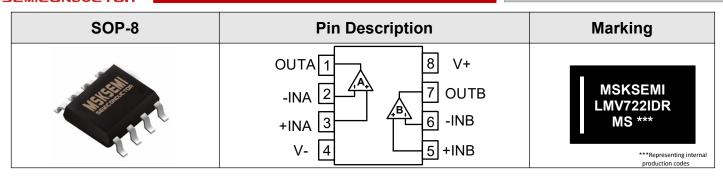
- Photodiode Amplification
- Active Filter and Buffer
- Battery Powered Electronics
- Sensors
- Cellular and Cordless Phones
- Test Equipment
- Driving A/D Converters

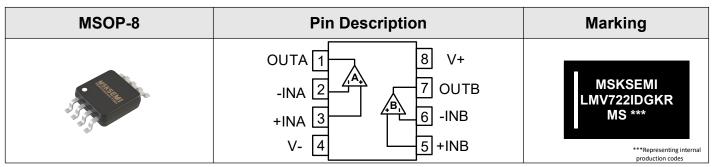
Pin Description AND MARKING

SC70-5	Pin Description	Marking
	OUT 1 5 V+ V- 2 + IN 3 4 - IN	<u>RKM</u>

SOT-23-5	Pin Description	Marking
WHITE WAY	OUT 1 5 V+ V- 2 + IN 3 4 - IN	R <u>B</u> <u>F</u> <u>M</u>







LMV721IDCKR-MS/LMV721IDBVR-MS

	PIN		I/O	DESCRIPTION		
NAME	SC70-5	SOT-23-5				
+IN	3		I	Positive (noninverting) input		
-IN	4		I	Negative (inverting) input		
OUT	1		0	Output		
V+	5		V+ 5		_	Positive (highest) power supply
V-	2		_	Negative (lowest) power supply		

LMV722IDR-MS/LMV722IDGKR-MS

PIN	1	I/O	DESCRIPTION
NAME	SOP-8 MSOP-8		Deskii nek
+INA	3	I	Noninverting input, channel A
+INB	5 I Noninverting input, ch		Noninverting input, channel B
-INA	2	I	Inverting input, channel A
-INB	6	I	Inverting input, channel B
OUTA	1	0	Output, channel A
OUTB	OUTB 7		Output, channel B
V- 4		_	Negative (lowest) power supply
V+	8	_	Positive (highest) power supply



Package/Order Information

ORDERING NUMBER	Op Temp(℃)	Package	Packing Option
LMV721IDCKR-MS	-55°C~125°C	SC70-5	3000PCS
LMV721IDBVR-MS		SOT23-5	3000PCS
LMV722IDR-MS		SOP-8	2500PCS
LMV722IDGKR-MS		MSOP-8	2500PCS

TYPICAL APPLICATION

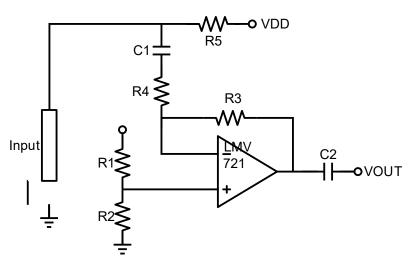


Figure 1. Typical Application



SPECIFICATIONS

Absolute Maximum Ratings(1)

		MIN	MAX	UNIT
	Supply Voltage		6	V
Voltage	Signal Input Terminals Voltage ⁽²⁾	(V-) - 0.5	(V+) + 0.5	V
	Signal Input Terminals Voltage ⁽³⁾	(V-) - 0.5	(V+) + 0.5	V
	Signal Input Terminals Current ⁽²⁾	-10	10	mA
Current	Signal output Terminals Current ⁽³⁾	-200	200	mA
	Output Short-Circuit ⁽⁴⁾	Contin	iuous	
	Operating Temperature Range	-40	85	°C
θја	Storage Temperature Range	-65	150	°C
	Junction Temperature	-40	150	°C

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) Input terminals are diode clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current limited to 10mA or less.
- (3) Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±200mA or less.
- (4) Short-circuit to ground, one amplifier per package.

ESD Ratings

			VALUE	UNIT
		Human-Body Model (HBM)	±2000	V
V _(ESD)	Electrostatic discharge	Charged-Device Model (CDM)	±500	V
		Machine Model	100	V

Recommended Operating Conditions

		MIN	MAX	UNIT
Supply voltage , Vs= (V+) -	Single-supply	2.2	5.5	V
(V-)	Dual-supply	±1.1	±2.75	V



ELECTRICAL CHARACTERISTICS(V_S = +5V)

At T_A = 25°C, V_{IN}=V_{OUT}= V_S /2, unless otherwise noted.

	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET V	OLTAGE					
Vos	Input Offset Voltage		-2.5	0.8	2.5	mV
dVos/dT	Input Offset Voltage Average Drift	T _A = -40°C to 85°C		0.6		μV/°C
INPUT CU	RRENT					
				10		рА
lв	Input Bias Current	T _A = -40°C to 85°C		4		pA/°C
los	Input Offset Current			5		рА
NOISE						
V_N	Input Voltage Noise	f=0.1Hz to 10Hz		4		μV _{PP}
	Input Voltage Noise PSD	f=1kHz		8		nV/√Hz
INPUT VO	LTAGE		<u> </u>			
Vсм	Common-Mode Voltage Range		(Vs-)- 0.1		(Vs+)+0.1	V
CMRR	Common-Mode Rejection Ratio	ΔV _{IN} =2V		90		dB
FREQUEN	CY RESPONSE					
GBW	Gain-Bandwidth Product			8		MHz
SR	Slew Rate	G = +1, V _{IN} =2V Step		6		V/µs
Ts	Settling Time	G = +1, V _{IN} =2V Step		0.6		us
OUTPUT						
Av	Open-Loop Voltage Gain	ΔV _{OUT} =4V	95	105		dB
V _{OUT} - swing	Output Swing from Rail				5	mV
	Output Short-Circuit	Sourcing, Vout=0V V _{IN(diff)} =±0.5V		26		mA
Isc	Current	Sinking, V _{OUT} =2.5V V _{IN(diff)} =±0.5V		50		mA



C _L ⁽¹⁾	Capacitive Load Drive	G=+1,V _{IN=} 0.2V Step			1000	pF
POWER SUPPLY						
PSRR	Power-Supply Rejection Ratio	V _S =2.5V to 5.5V	90	110		dB
Vs	Operating Voltage Range	lo=0A	2.2		5.5	V
la	Quiescent Current/Amplifier	lo=0A		510	600	μA

⁽¹⁾ Capacitive load drive means that above a given maximum value, the output waveform will oscillate under the step response.



ELECTRICAL CHARACTERISTICS(V_S = +2.5V)

At $T_A = 25$ °C, $V_{IN}=V_{OUT}=V_S/2$, unless otherwise noted.

	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET V	OLTAGE					
Vos	Input Offset Voltage			0.18	2.5	mV
dV _{OS} /dT	Input Offset Voltage Average Drift	T _A = -40°C to 85°C		0.4	0.6	μV/°C
INPUT CU	RRENT					
				200	700	pA
l _B	Input Bias Current	T _A = -40°C to 85°C		4		pA/°C
los	Input Offset Current			200		pA
NOISE						
V _N	Input Voltage Noise	f=0.1Hz to 10Hz		15		μV _{PP}
	Input Voltage Noise PSD	f=1kHz		61		nV/√Hz
INPUT VO	LTAGE				1	
Vсм	Common-Mode Voltage Range		(VS-)- 0.1		(VS+)+0.1	V
CMRR	Common-Mode Rejection Ratio	ΔV _{IN} =1V	80	90		dB
FREQUEN	ICY RESPONSE					
GBW	Gain-Bandwidth Product			6.5		MHz
SR	Slew Rate			5		V/µs
Ts	Settling Time			0.8		us
ОИТРИТ					1	
Av	Open-Loop Voltage Gain	ΔV _{OUT} =2V	105	110		dB
V _{OUT} -	Output Swing from Rail				5	mV
loc	Output Short-Circuit	Sourcing, V _{OUT} =0V V _{IN(diff)} =±0.5V		11		mA
Isc	Current	Sinking, V _{OUT} =2.2V V _{IN(diff)} =±0.5V		- 16.6		mA

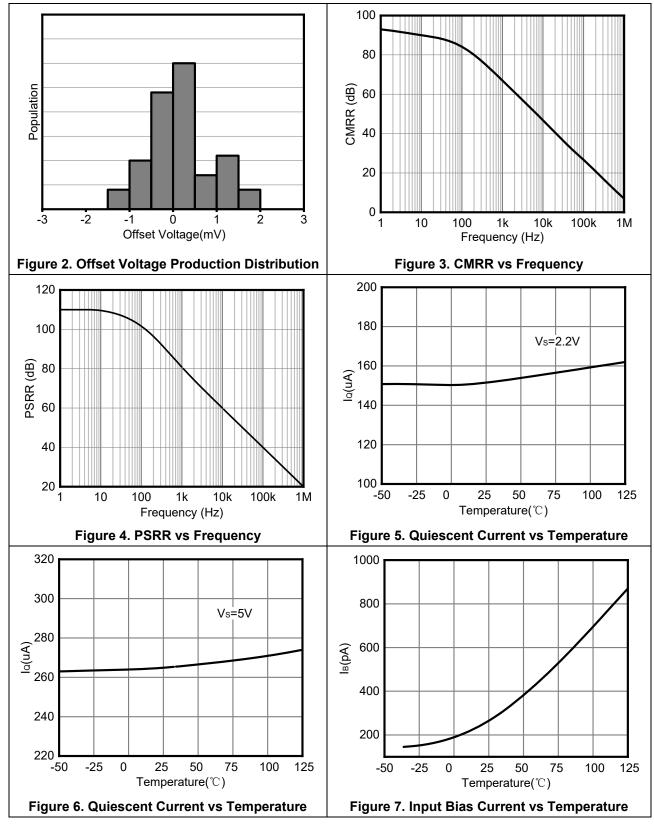


C _L ⁽¹⁾	Capacitive Load Drive	G = +1, V _{IN} =1V Step			100	pF
POWER SUPPLY						
PSRR	Power-Supply Rejection Ratio	Vs=2.5V to 5.5V	90	110		dB
Vs	Operating Voltage Range	lo=0A	2.2		5.5	V
lQ	Quiescent Current/Amplifier	l _O =0A		510	600	μA



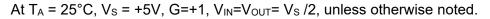
TYPICAL CHARACTERISTICS

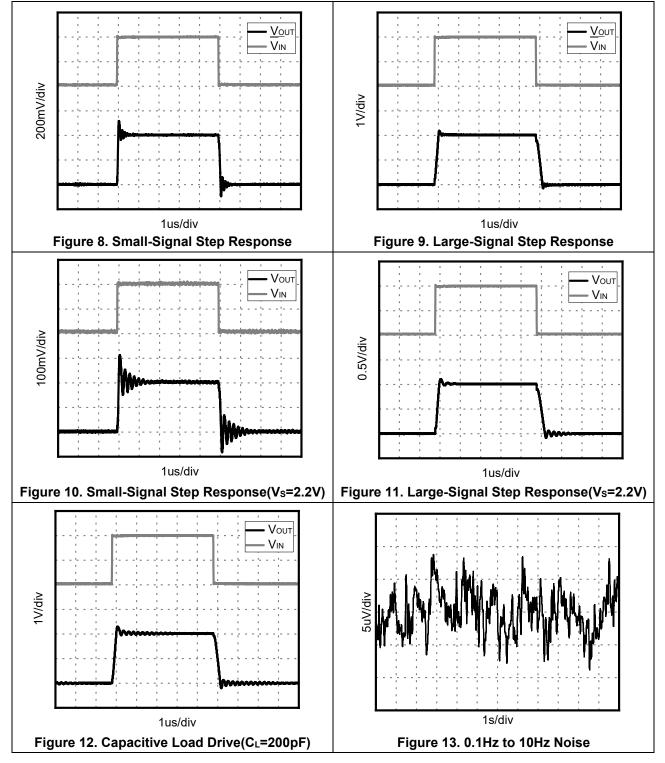
At $T_A = 25$ °C, $V_S = +5V$, G=+1, $V_{IN}=V_{OUT}=V_S/2$, unless otherwise noted.





TYPICAL CHARACTERISTICS

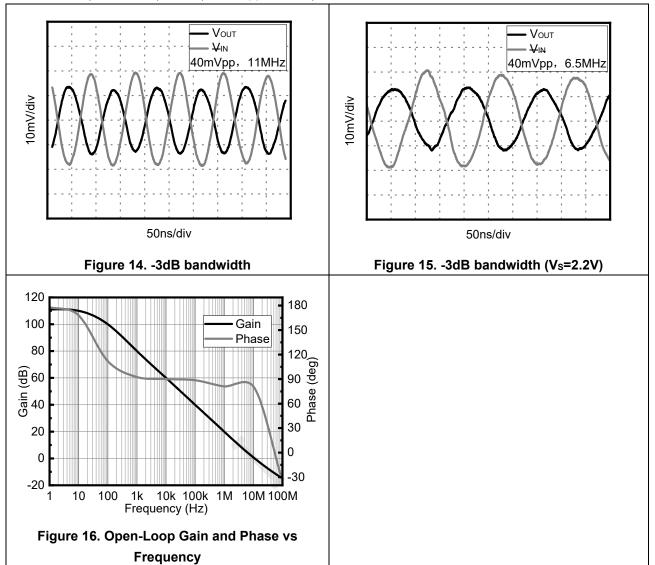






TYPICAL CHARACTERISTICS

At $T_A = 25$ °C, $V_S = +5V$, G=+1, $V_{IN}=V_{OUT}=V_S/2$, unless otherwise noted.





Detailed Description

Overview

The LMV721/LMV722 devices are a high-bandwidth, unity-gain stable, rail-to-rail operational a mplifier available in single and dual-channel versions that operate in a single-supply voltage range of 2.2V to 5.5V(±1.1V to ±2.75V). A high supply voltage of 6V(absolute maximum) can permanently d amage the amplifier. Rail-to-rail input and output wobbles significantly increase the dynamic r ange, especially in low-supply applications. Good layout practices require that a 0.1uF capacitor be used where it is tightly threaded through the power supply pin.

Phase Reversal Protection

The LMV721/LMV722 devices have internal phase-reversal protection.

Many op amps exhibit phase reversal when the input is driven beyond the linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven b eyond the specified common-mode voltage range,

causing the output to reverse into the opposite rail. The input of the LMV721/LMV722 prevents phase reversal with excessive commonmode voltage. Instead, the appropriate rail limits the output voltage.

Typical Applications

1 Voltage Follower

As shown in Figure 17, the voltage gain is 1. With this circuit, the output voltage V_{OUT} is configured to be equal to the input voltage V_{IN} . Due to the high input impedance and low output impedance, the circuit can also stabilize the output voltage, the output voltage expression is

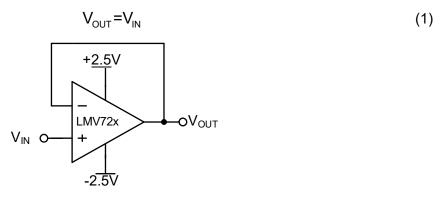


Figure 17. Voltage Follower

2 Inverting Proportional Amplifier

As shown in Figure 18, for a reverse-phase proportional amplifier, the input voltage V_{IN} is amplified by a voltage gain that depends on the ratio of R1 to R2. The output voltage V_{OUT} is inversely with the input voltage V_{IN} . The input impedance of the circuit is equal to R1, and the output voltage expression is

$$V_{OUT} = -\frac{R2}{R1}V_{IN}$$
 (2)



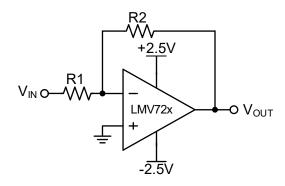


Figure 18. Inverting Proportional Amplifier

3 Noninverting Proportional Amplifier

As shown in Figure 19, for a noninverting amplifier, the input voltage V_{IN} is amplified by a voltage gain that depends on the ratio of R1 to R2. The output voltage V_{OUT} is in phase with the input voltage V_{IN} . In fact, this circuit has a high input impedance because its input side is the same as the input side of the operational amplifier. The output voltage expression is

$$V_{OUT} = (1 + \frac{R2}{R1})V_{IN}$$
 (3)

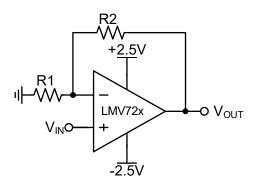


Figure 19. Noninverting Proportional Amplifier

Layout Guidelines

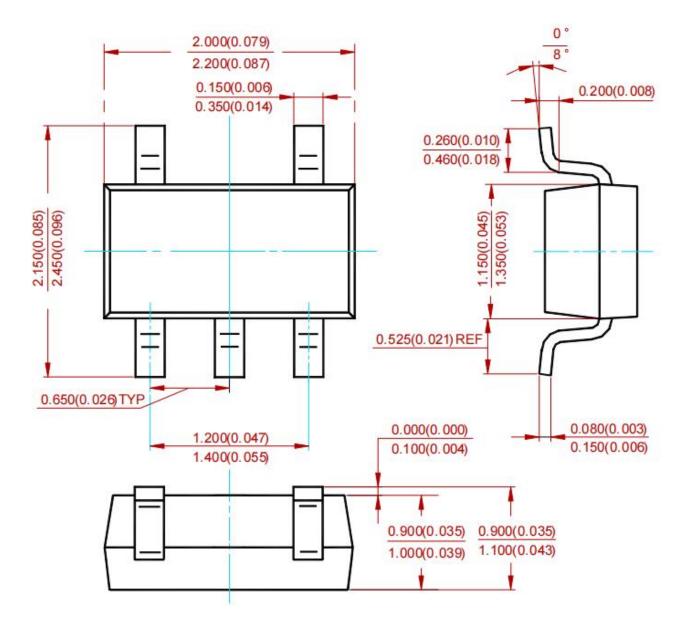
Attention to good layout practices is always recommended. Keep traces short. When possible, use a PCB ground plane with surface-mount components placed as close to the device pins as possible. Place a 0.1uF capacitor closely across the supply pins.

These guidelines should be applied throughout the analog circuit to improve performance and provide benefits such as reducing the EMI susceptibility.



Package Outline Dimensions (All dimensions in mm(inch).)

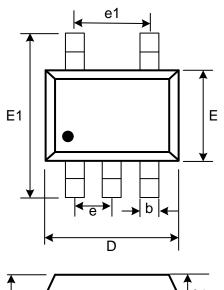
SC-70-5

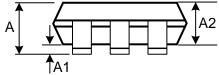


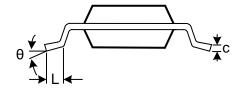


Package Description

SOT23-5





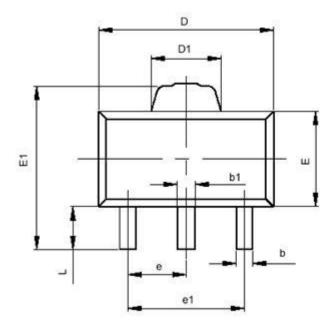


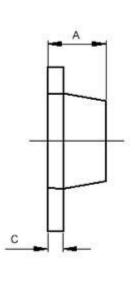
(Unit: mm)

Symbol	Min	Max		
А	1.05	1.25		
A1	0	0.1		
A2	1.05	1.15		
b	0.3	0.5		
С	0.1	0.2		
D	2.82	3.02		
е	0.95(BSC)			
e1	1.9(BSC)			
E	1.5	1.7		
E1	2.65	2.95		
L	0.3	0.6		
θ	0°	8°		



SOT-89-3

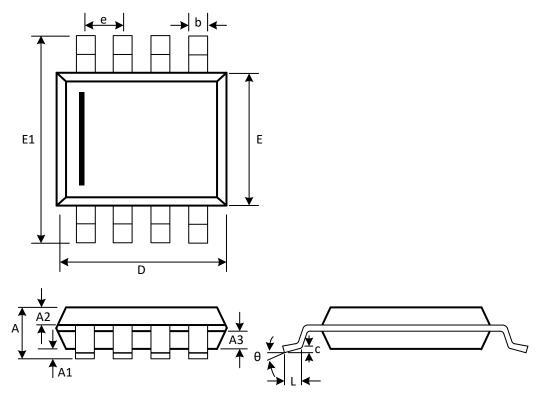




符号	最小值(mm)	最大值(mm)		
Α	1.400	1.600		
ь	0.320	0.520		
b1	0.360	0.560		
С	0.350	0.440		
D	4.400	4.600		
D1	1.400	1.800		
E	2.300	2.600		
E1	3.940	4.250		
е	1.500TYP			
e1	2.900	3.100		
L	0.900	1.100		



SOP-8

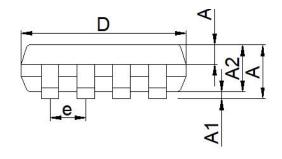


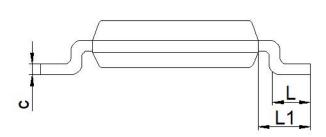
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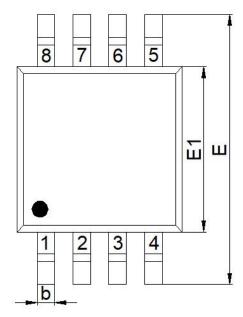
Symbol	Min	Max		
А	1.300	1.600		
A1	0.050	0.200		
A2	0.550	0.650		
А3	0.550	0.650		
b	0.356	0.456		
С	0.203	0.233		
D	4.800	5.000		
е	1.270(BSC)			
E	3.800	4.000		
E1	5.800	6.200		
L	0.400	0.800		
θ	0°	8°		



MSOP8 封装外形尺寸







MSOP8 外形图

单位: mm

项目	尺寸			尺寸			
	Min.	Тур.	Max.	项目	Min.	Тур.	Max.
A			1.10	D	2.90	3.00	3.10
A1	0.05		0.15	Е	4.70	4.90	5.10
A2	0.75	0.85	0.95	E1	2.90	3.00	3.10
A3	0.30	0.35	0.40	e		0.65	
b	0.28		0.38	L	0.40		0.70
c	0.15		0.19	L1		0.95	



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